

Title (en)  
SEMICONDUCTOR OPTICAL AMPLIFIER

Title (de)  
OPTISCHER HALBLEITERVERSTÄRKER

Title (fr)  
AMPLIFICATEUR OPTIQUE EN SEMI-CONDUCTEUR

Publication  
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Application  
**EP 01963109 A 20010820**

Priority  
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Abstract (en)  
[origin: WO0217453A1] The invention concerns a semiconductor optical amplifier comprising a buried active guide structure (12). The invention is characterised in that an external strain is applied to said active guide structure (12) such that it is subjected to a global strain which makes said amplifier insensitive to the polarisation of the light to be amplified, said external constraint resulting from a force induced by deposit of a material (50) against the stripe (15) enclosing said active guide structure (12).

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